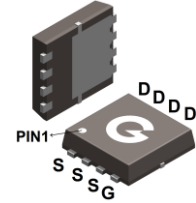
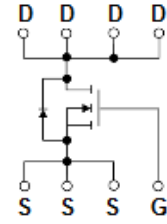


Features

- Advanced shielded-gate technology
- Ultra-low on-resistance and gate-charge
- 100% avalanche tested
- HBM: JESD22-A114-B: 1A
- RoHS compliant with Halogen-free

HF



PDFN3x3-8L

Mechanical Data

- Case: PDFN3x3-8L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matted-Tin plated; Solderable Per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL050N03T-3DL8	PDFN3x3-8L	5000 pcs / Tape & Reel	050N03T

Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	30	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (T _C = 25°C)	I _D	64	A
Continuous Drain Current (T _C = 100°C)		40	
Continuous Drain Current (T _A = 25°C) ^{*1}		19	
Continuous Drain Current (T _A = 100°C) ^{*1}		12	
Pulsed Drain Current (t _p = 10μs, T _C = 25°C)	I _{DM}	256	A
Pulsed Drain Current (t _p = 10μs, T _A = 25°C)		170	
Single Pulse Avalanche Energy ^{*3}	E _{AS}	27	mJ
Power Dissipation (T _C = 25°C)	P _D	31	W
Power Dissipation (T _A = 25°C) ^{*1}		2.8	
Operating Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	R _{θJC}	-	-	4	°C/W
Thermal Resistance Junction-to-Air ^{*1}	R _{θJA}	-	-	45	°C/W

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 30V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *2	V _{GS} = 10V, I _D = 30A	-	4.6	5	mΩ
		V _{GS} = 4.5V, I _D = 20A	-	6.5	8	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1	1.5	2	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	4	-	Ω
Dynamic Characteristics						
g _{fs}	Forward Transconductance	V _{DS} = 5V, I _D = 20A	-	85	-	S
C _{ISS}	Input Capacitance	V _{GS} = 0V	-	1081	-	pF
C _{OSS}	Output Capacitance	V _{DS} = 15V	-	482	-	
C _{RSS}	Reverse Transfer Capacitance	f = 1MHz	-	26	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time *4	V _{DD} = 15V	-	7	-	ns
t _r	Turn-on Rise Time *4	V _{GS} = 10V	-	2.8	-	
t _{d(OFF)}	Turn-Off Delay Time *4	R _G = 3Ω	-	21.4	-	
t _f	Turn-Off Fall Time *4	I _D = 15A	-	5.3	-	
Q _G	Total Gate-Charge	V _{DD} = 15V	-	16.3	-	nC
Q _{GS}	Gate to Source Charge	I _D = 20A	-	2.9	-	
Q _{GD}	Gate to Drain (Miller) Charge	V _{GS} = 10V	-	2.4	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *2	I _{SD} = 20A, V _{GS} = 0V	-	0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} = 20A, V _{GS} = 0V	-	79	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt = 100A/μs	-	51	-	nC

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 30V, V_{GS} = 10V, L = 0.5mH$
4. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

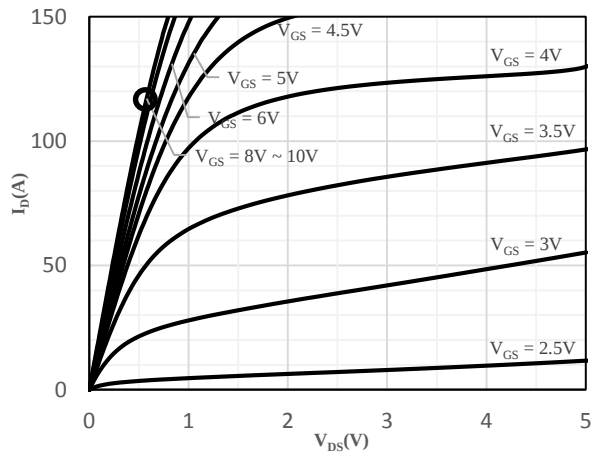


Fig 1 Typical Output Characteristics

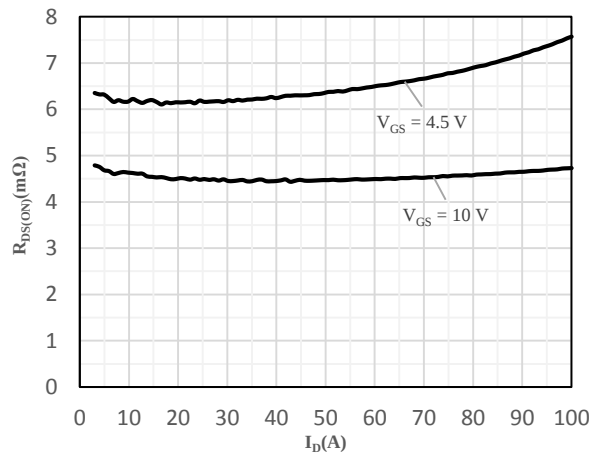


Fig 2 On-Resistance vs. Drain Current and Gate Voltage

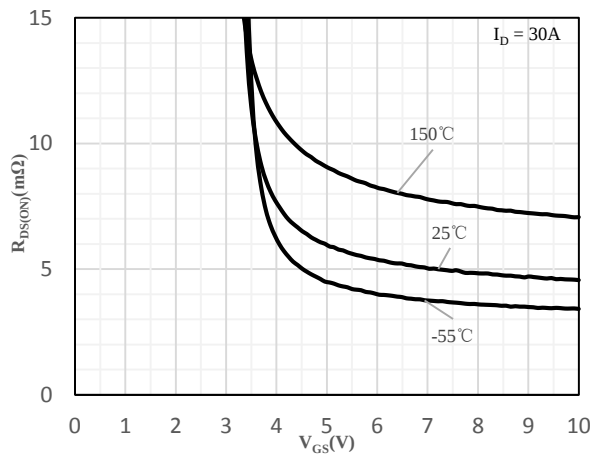


Fig 3 On-Resistance vs. Gate-Source Voltage

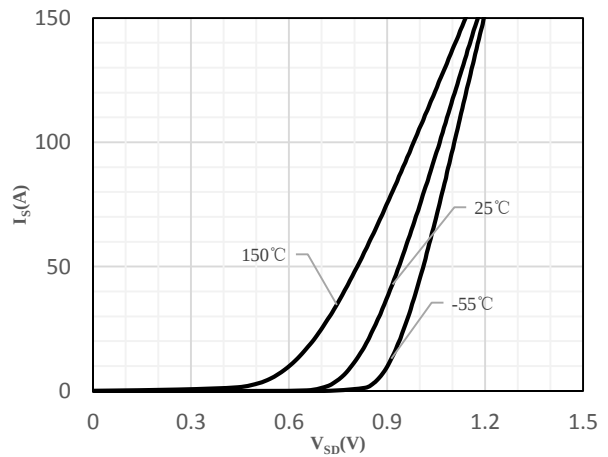


Fig 4 Body-Diode Characteristics

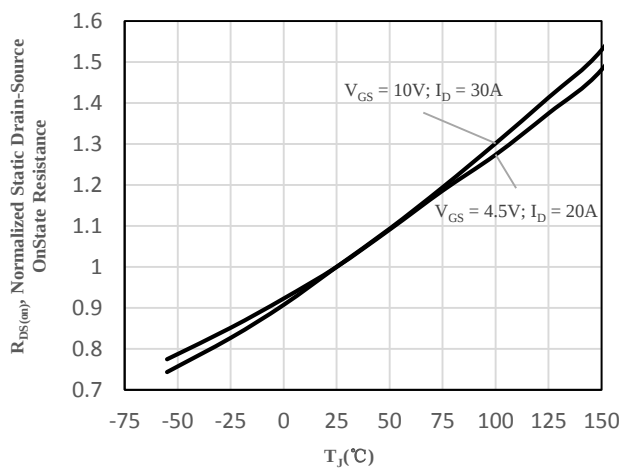


Fig 5 Normalized On-Resistance vs. Junction Temperature

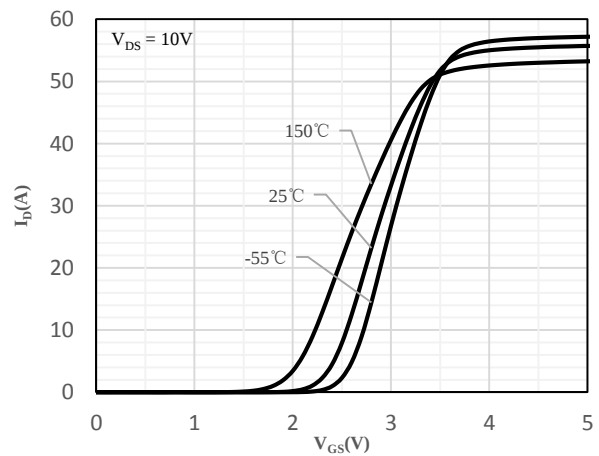


Fig 6 Transfer Characteristics

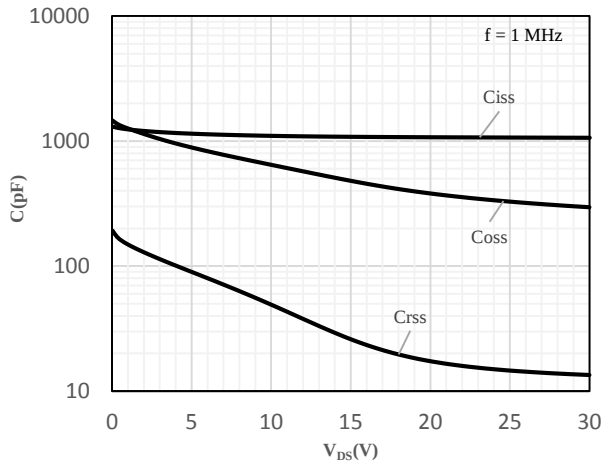


Fig 7 Capacitance Characteristics

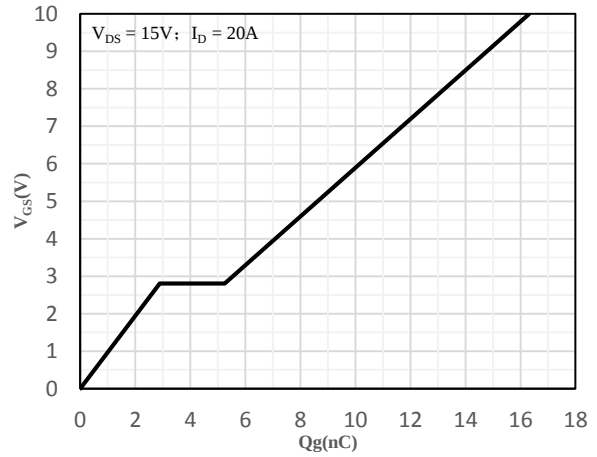


Fig 8 Gate-Charge Characteristics

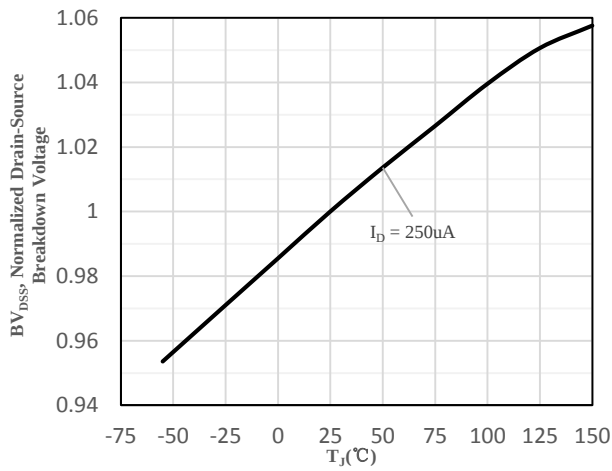


Fig 9 Normalized Breakdown Voltage vs. Junction Temperature

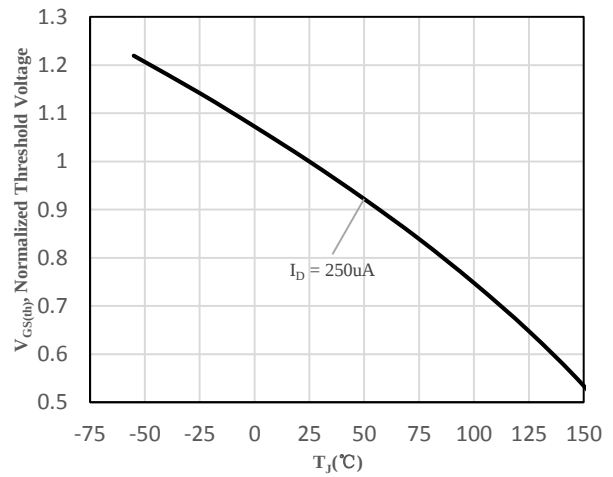


Fig 10 Normalized $V_{GS(th)}$ vs. Junction Temperature

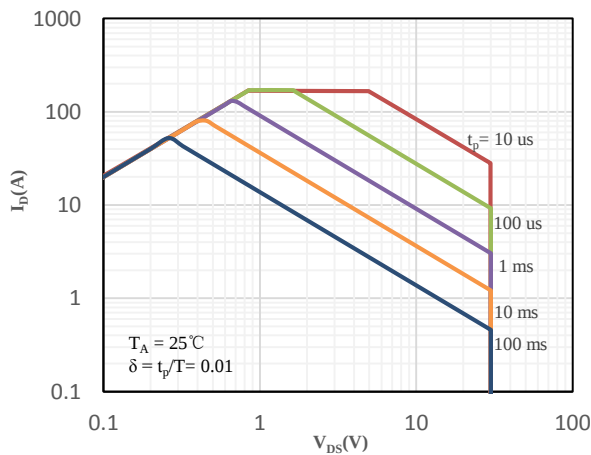


Fig 11 Safe Operating Area

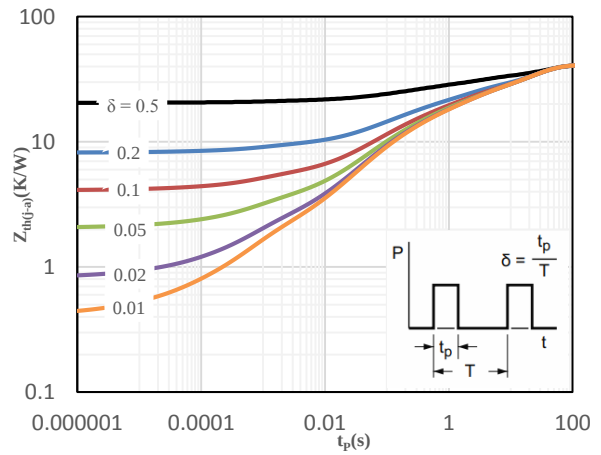
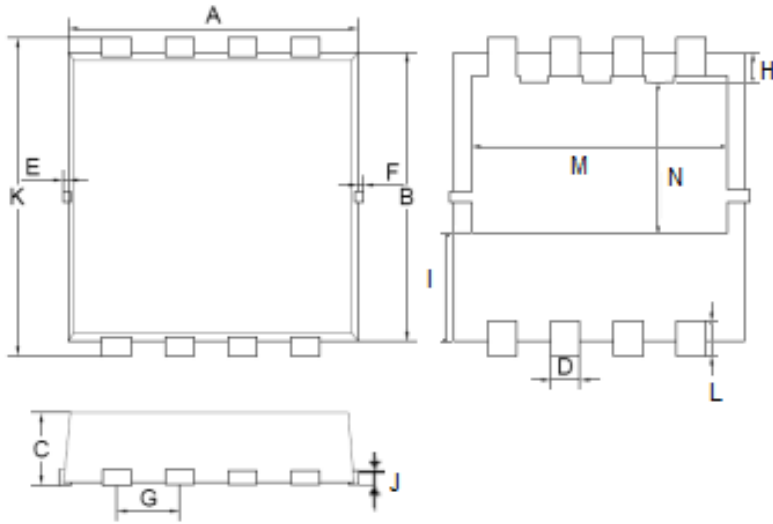


Fig 12 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



PDFN3x3-8L		
Dimension	Min.	Max.
A	2.90	3.10
B	2.90	3.10
C	0.65	0.85
D	0.20	0.40
E	0.00	0.10
F	0.00	0.10
G	0.55	0.75
H	0.20	0.40
I	0.70	1.10
J	0.10	0.20
K	3.15	3.45
L	0.20	0.40
M	2.35	2.55
N	1.500	1.900

Mounting Pad Layout (Unit: mm)

PDFN3x3-8L

